

Stud Diode

Rectifier Diode

SKN 71 SKR 71

Features

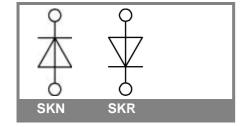
- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Threaded stud ISO M8 and also 1/4-28 UNF
- SKN: anode to stud, SKR: cathode to stud

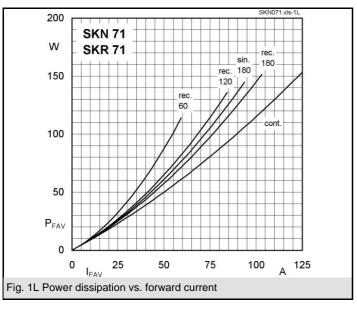
Typical Applications

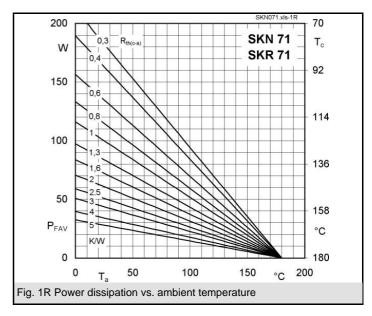
- All-purpose mean power rectifier diodes
- · Cooling via heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes
- Recommended snubber network: RC: 0,1 μ F, 100 Ω (P $_{R}$ = 2 W), R $_{P}$ = 80 $k\Omega$ (P $_{R}$ = 6 W)

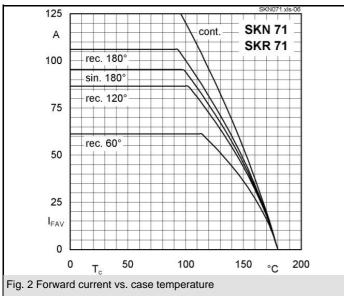
V _{RSM}	V _{RRM}	I _{FRMS} = 150 A (maximum value for continuous operation)		
V	V	I _{FAV} = 70 A (sin. 180; T _c = 125 °C)		
400	400	SKN 71/04	SKR 71/04	
800	800	SKN 71/08	SKR 71/08	
1200	1200	SKN 71/12	SKR 71/12	
1400	1400	SKN 71/14	SKR 71/14	
1600	1600	SKN 71/16	SKR 71/16	

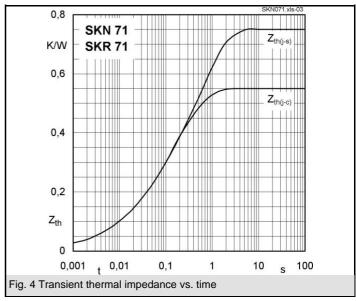
Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _c = 100 °C	95	Α
I_D	K 1,1; T _a = 45 °C; B2 / B6	112 / 159	Α
	K 1,1F; T _a = 35 °C; B2 / B6	174 / 246	Α
I _{FSM}	T _{vi} = 25 °C; 10 ms	1150	Α
	T _{vi} = 180 °C; 10 ms	1000	Α
i²t	T _{vj} = 25 °C; 8,3 10 ms	6600	A²s
	T _{vj} = 180 °C; 8,3 10 ms	5000	A²s
V _F	T _{vi} = 25 °C; I _F = 200 A	max. 1,5	V
V _(TO)	T _{vi} = 180 °C	max. 0,85	V
r _T	T _{vi} = 180 °C	max. 3	$m\Omega$
I_{RD}	$T_{vj} = 180 ^{\circ}\text{C}; V_{RD} = V_{RRM}$	max. 10	mA
Q_{rr}	$T_{vj} = 160 ^{\circ}\text{C}$; - $di_F/dt = 10 \text{A/}\mu\text{s}$	70	μC
R _{th(j-c)}		0,55	K/W
R _{th(c-s)}		0,2	K/W
T _{vj}		- 40 + 180	°C
T _{stg}		- 55 + 180	°C
V _{isol}		-	V~
M _s	to heatsink	4	Nm
а		5 * 9,81	m/s²
m	approx.	30	g
Case		E 11	

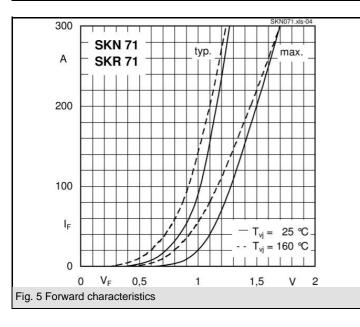


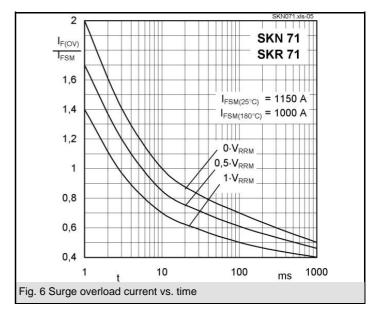


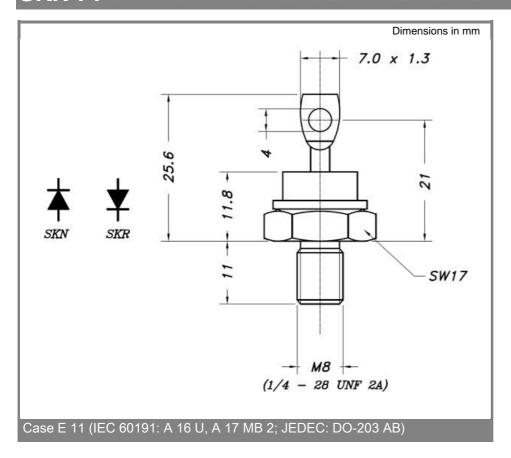












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